





Typical Performance Characteristics

$I_D$ - Drain Current (A)

$V_{ds}$  Drain-Source Voltage (V)  
Figure 1 Output Characteristics

$I_D$ - Drain Current (A)

$V_{gs}$  Gate-Source Voltage (V)  
Figure 2 Transfer Characteristics

$R_{ds(on)}$  On-Resistance(m $\Omega$ )

$I_D$ - Drain Current (A)  
Figure 3  $R_{ds(on)}$ - Drain Current

Normalized On-Resistance

$T_J$ -Junction Temperature( )  
Figure 4  $R_{ds(on)}$ -Junction Temperature

$V_{gs}$  Gate-Source Voltage (V)

$Q_g$  Gate Charge (nC)  
Figure 5 Gate Charge

$I_S$ - Reverse Drain Current (A)

$V_{sd}$  Source-Drain Voltage (V)  
Figure 6 Source- Drain Diode Forward

C Capacitance (pF)

Vds Drain-Source Voltage (V)  
Figure 7 Capacitance vs Vds

Power Dissipation (W)

T<sub>J</sub>-Junction Temperature( )  
Figure 9 Power De-rating

I<sub>D</sub>- Drain Current (A)

Vds Drain-Source Voltage (V)  
Figure 8 Safe Operation Area

T<sub>J</sub>-Junction Temperature( )  
Figure 10 ID Current- JunctionTemperature

r(t), Normalized Effective  
Transient Thermal Impedance

Package Information:TO-252-3L

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
-	1.100	1.300	0.043	0.051
	e	e	e	e
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	